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Electronic correlation effects in SrRuO₃ ultra-thin films LIANG

SI, Institute of Solid State Physics, Vienna University of Technology, ZHICHENG ZHONG, Max Planck Institute for Solid State Research, OLEG JANSON, GANG LI, JAN TOMCZAK, KARSTEN HELD, Institute of Solid State Physics, Vienna University of Technology, COMPUTATIONAL MATERIALS SCIENCE TEAM, ELECTRONIC STRUCTURE OF CORRELATED MATERIALS TEAM — SrRuO₃ (SRO) is a ferromagnetic metal with an appreciably high Curie-temperature of 160 K and a ferromagnetic moment of 0.8-1.6 μ_B /Ru. Recent experimental studies on SRO thin films show that both electronic and magnetic ground states drastically depend on the nature of the surface. Ultra-thin (001)-oriented films are insulating and lack ferromagnetism, while in (111)-oriented films ferromagnetic moments and T_c are enhanced compared with bulk. Here we investigate SRO films by density functional theory (DFT)+U and DFT+dynamical mean-field theory (DMFT). In agreement with the experiments, we find that metallic ferromagnetism in SRO (001)-oriented films vanishes below a certain critical layer thickness. We propose a new route for tuning the properties of these thin films and show that room temperature ferromagnetism can be attained by electron doping. For the SRO (111)-oriented thin films, we find that the enhanced T_c is facilitated by electronic correlation effects and the geometric confinement. The experimentally observed enhancement of ferromagnetic moments in SRO(111)-oriented thin films is addressed by considering the stability of the high-spin Ru state in the presence of oxygen vacancies. Finally, the topological properties of SRO (111)-oriented bilayers will be discussed.

Liang Si
Vienna Univ of Technology

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